# **CD4078BMS**

December 1992

# **CMOS 8 Input NOR/OR Gate**

#### **Features**

- High Voltage Type (20V Rating)
- Medium Speed Operation
  - tPHL, tPLH = 75ns (Typ.) at VDD = 10V
- · Buffered Inputs and Output
- 5V, 10V and 15V Parametric Ratings
- · Standardized, Symmetrical Output Characteristics
- 100% Tested for Quiescent Current at 20V
- Maximum Input Current of 1μA at 18V Over Full Package Temperature Range; 100nA at 18V and +25°C
- Noise Margin (Over Full Package/Temperature Range)
  - 1V at VDD = 5V
  - 2V at VDD = 10V
  - 2.5V at VDD = 15V
- Meets All Requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

# Description

CD4078BMS NOR/OR Gate provides the system designer with direct implementation of the positive logic 8 input NOR and OR functions and supplements the existing family of CMOS gates.

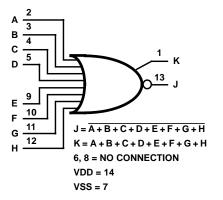
The CD4078BMS is supplied in these 14 lead outline packages:

Braze Seal DIP H4Q
Frit Seal DIP H1B
Ceramic Flatpack H3W

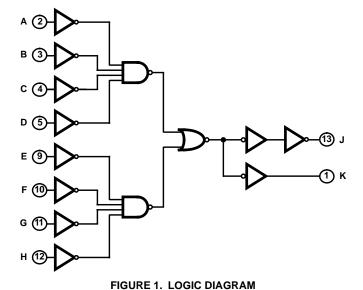
# Pinout CD4078BMS TOP VIEW K\*\* 1 A 2 B 3 C 4 D 5 NC 6 VSS 7 B NC \* J=A+B+C+D+E+F+G+H \*\*K=A+B+C+D+E+F+G+H

# Functional Diagram

NC = NO CONNECTION



# Logic Diagram



#### **Reliability Information Absolute Maximum Ratings** Thermal Resistance ..... nermal Resistance . . . . . . . . . . . $\theta_{ja}$ Ceramic DIP and FRIT Package . . . . $80^{\circ}$ C/W DC Supply Voltage Range, (VDD) . . . . . -0.5V to +20V (Voltage Referenced to VSS Terminals) Input Voltage Range, All Inputs . . . . . . . . -0.5V to VDD +0.5V Flatpack Package . . . . . . . . . . . . . . . . . 70°C/W 20°C/W DC Input Current, Any One Input .....±10mA Maximum Package Power Dissipation (PD) at +125°C Operating Temperature Range.....-55°C to +125°C For TA = $-55^{\circ}$ C to $+100^{\circ}$ C (Package Type D, F, K).....500mW For TA = $+100^{\circ}$ C to $+125^{\circ}$ C (Package Type D, F, K) . . . . . Derate Package Types D, F, K, H Storage Temperature Range (TSTG) . . . . . . . -65°C to +150°C Linearity at 12mW/°C to 200mW Lead Temperature (During Soldering) . . . . . . . . +265°C Device Dissipation per Output Transistor . . . . . . . . . . . . . . . . 100mW For TA = Full Package Temperature Range (All Package Types) At Distance 1/16 $\pm$ 1/32 Inch (1.59mm $\pm$ 0.79mm) from case for 10s Maximum

#### TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

				GROUP A		LIMITS		
PARAMETER	SYMBOL	CONDITIONS (	NOTE 1)	SUBGROUPS	TEMPERATURE	MIN	MAX	UNITS
Supply Current	IDD	VDD = 20V, VIN = VDD or GND		1	+25°C	-	0.5	μΑ
				2	+125°C	-	50	μΑ
		VDD = 18V, VIN = VD	D or GND	3	-55°C	-	0.5	μΑ
Input Leakage Current	IIL	VIN = VDD or GND	VDD = 20	1	+25°C	-100	-	nA
				2	+125°C	-1000	-	nA
			VDD = 18V	3	-55°C	-100	-	nA
Input Leakage Current	IIH	VIN = VDD or GND	VDD = 20	1	+25°C	-	100	nA
				2	+125°C	-	1000	nA
			VDD = 18V	3	-55°C	-	100	nA
Output Voltage	VOL15	VDD = 15V, No Load		1, 2, 3	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOH15	VDD = 15V, No Load	(Note 3)	1, 2, 3	+25°C, +125°C, -55°C	14.95	-	V
Output Current (Sink)	IOL5	VDD = 5V, VOUT = 0.	.4V	1	+25°C	0.53	-	mA
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0.5V		1	+25°C	1.4	-	mA
Output Current (Sink)	IOL15	VDD = 15V, VOUT = 1.5V		1	+25°C	3.5	-	mA
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V		1	+25°C	-	-0.53	mA
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.5V		1	+25°C	-	-1.8	mA
Output Current (Source)	IOH10	VDD = 10V, VOUT = 9	9.5V	1	+25°C	-	-1.4	mA
Output Current (Source)	IOH15	VDD = 15V, VOUT = 1	13.5V	1	+25°C	-	-3.5	mA
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10	)μΑ	1	+25°C	-2.8	-0.7	V
P Threshold Voltage	VPTH	VSS = 0V, IDD = 10μ/	A	1	+25°C	0.7	2.8	V
Functional	F	VDD = 2.8V, VIN = VI	DD or GND	7	+25°C	VOH>	VOL <	V
		VDD = 20V, VIN = VD	D or GND	7	+25°C	VDD/2 VDD/	VDD/2	
		VDD = 18V, VIN = VD	D or GND	8A	+125°C			
		VDD = 3V, VIN = VDD	or GND	8B	-55°C			
Input Voltage Low (Note 2)	VIL	VDD = 5V, VOH > 4.5V, VOL < 0.5V		1, 2, 3	+25°C, +125°C, -55°C	-	1.5	٧
Input Voltage High (Note 2)	VIH	VDD = 5V, VOH > 4.5V, VOL < 0.5V		1, 2, 3	+25°C, +125°C, -55°C	3.5	-	٧
Input Voltage Low (Note 2)	VIL	VDD = 15V, VOH > 13 VOL < 1.5V	3.5V,	1, 2, 3	+25°C, +125°C, -55°C	-	4	٧
Input Voltage High (Note 2)	VIH	VDD = 15V, VOH > 13 VOL < 1.5V	3.5V,	1, 2, 3	+25°C, +125°C, -55°C	11	-	V

NOTES: 1. All voltages referenced to device GND, 100% testing being 3. For accuracy, voltage is measured differentially to VDD. Limit implemented.

is 0.050V max.

2. Go/No Go test with limits applied to inputs.

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

			GROUP A	GROUP A		LIMITS		
PARAMETER	SYMBOL	CONDITIONS (NOTES 1, 2)	SUBGROUPS	TEMPERATURE	MIN	MAX	UNITS	
Propagation Delay	TPHL	VDD = 5V, VIN = VDD or GND	9	+25°C	-	300	ns	
	TPLH		10, 11	+125°C, -55°C	-	405	ns	
Transition Time	TTHL	VDD = 5V, VIN = VDD or GND	9	+25°C	-	200	ns	
TTLH			10, 11	+125°C, -55°C	-	270	ns	
Maximum Clock Input	FCL	VDD = 5V, VIN = VDD or GND	9	+25°C	3	-	MHz	
Frequency			10, 11	+125°C, -55°C	2.22	-	MHz	

### NOTES:

- 1. VDD = 5V, CL = 50pF, RL = 200K
- 2. -55°C and +125°C limits guaranteed, 100% testing being implemented.

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

					LIN	IITS	
PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	MIN	MAX	UNITS
Supply Current	IDD	VDD = 5V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	0.25	μΑ
				+125°C	-	7.5	μΑ
		VDD = 10V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	0.5	μΑ
				+125°C	-	15	μΑ
		VDD = 15V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	0.5	μΑ
				+125°C	-	30	μΑ
Output Voltage	VOL	VDD = 5V, No Load	1, 2	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOL	VDD = 10V, No Load	1, 2	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOH	VDD = 5V, No Load	1, 2	+25°C, +125°C, -55°C	4.95	-	V
Output Voltage	VOH	VDD = 10V, No Load	1, 2	+25°C, +125°C, -55°C	9.95	-	V
Output Current (Sink)	IOL5	VDD = 5V, VOUT = 0.4V	1, 2	+125°C	0.36	-	mA
				-55°C	0.64	-	mA
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0.5V	1, 2	+125°C	0.9	-	mA
				-55°C	1.6	-	mA
Output Current (Sink)	IOL15	VDD = 15V, VOUT = 1.5V	1, 2	+125°C	2.4	-	mA
				-55°C	4.2	-	mA
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V	1, 2	+125°C	-	-0.36	mA
				-55°C	-	-0.64	mA
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.5V	1, 2	+125°C	-	-1.15	mA
				-55°C	-	-2.0	mA
Output Current (Source)	IOH10	VDD = 10V, VOUT = 9.5V	1, 2	+125°C	-	-0.9	mA
				-55°C	-	-1.6	mA
Output Current (Source)	IOH15	VDD =15V, VOUT = 13.5V	1, 2	+125°C	-	-2.4	mA
				-55°C	-	-4.2	mA
Input Voltage Low	VIL	VDD = 10V, VOH > 9V, VOL < 1V	1, 2	+25°C, +125°C, -55°C	-	3	V

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

					LIMITS		
PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	MIN	MAX	UNITS
Input Voltage High	VIH	VDD = 10V, VOH > 9V, VOL < 1V	1, 2	+25°C, +125°C, -55°C	7	-	V
Propagation Delay	TPHL	VDD = 10V	1, 2, 3	+25°C	-	150	ns
TPLH		VDD = 15V	1, 2, 3	+25°C	-	110	ns
Transition Time TTHL TTLH		VDD = 10V	1, 2, 3	+25°C	-	100	ns
		VDD = 15V	1, 2, 3	+25°C	-	80	ns
Maximum Clock Input	FCL	VDD = 10V	1, 2, 3	+25°C	6	-	MHz
Frequency		VDD = 15V	1, 2, 3	+25°C	8.5	-	MHz
Input Capacitance	CIN	ut	1, 2	+25°C	-	7.5	pF

#### NOTES:

- 1. All voltages referenced to device GND.
- 2. The parameters listed on Table 3 are controlled via design or process and are not directly tested. These parameters are characterized on initial design release and upon design changes which would affect these characteristics.
- 3. CL = 50pF, RL = 200K, Input TR, TF < 20ns.

TABLE 4. POST IRRADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS

					LIMITS		
PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	MIN	MAX	UNITS
Supply Current	IDD	VDD = 20V, VIN = VDD or GND	1, 4	+25°C	-	2.5	μΑ
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10μA	1, 4	+25°C	-2.8	-0.2	V
N Threshold Voltage Delta	ΔVTN	VDD = 10V, ISS = -10μA	1, 4	+25°C	-	±1	V
P Threshold Voltage	VTP	VSS = 0V, IDD = 10μA	1, 4	+25°C	0.2	2.8	V
P Threshold Voltage Delta	ΔVTP	VSS = 0V, IDD = 10μA	1, 4	+25°C	-	±1	V
Functional	F	VDD = 18V, VIN = VDD or GND	1	+25°C	VOH >	VOL <	V
		VDD = 3V, VIN = VDD or GND			VDD/2	VDD/2	
Propagation Delay Time	TPHL TPLH	VDD = 5V	1, 2, 3, 4	+25°C	-	1.35 x +25°C Limit	ns

NOTES: 1. All voltages referenced to device GND.

3. See Table 2 for +25°C limit.

2. CL = 50pF, RL = 200K, Input TR, TF < 20ns.

4. Read and Record

TABLE 5. BURN-IN AND LIFE TEST DELTA PARAMETERS +25°C

PARAMETER	SYMBOL	DELTA LIMIT
Supply Current - SSI	IDD	± 0.1μA
Output Current (Sink)	IOL5	± 20% x Pre-Test Reading
Output Current (Source)	IOH5A	± 20% x Pre-Test Reading

#### **TABLE 6. APPLICABLE SUBGROUPS**

CONFORMANCE GROUP	MIL-STD-883 METHOD	GROUP A SUBGROUPS	READ AND RECORD
Initial Test (Pre Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A

**TABLE 6. APPLICABLE SUBGROUPS** 

CONFORMANCE GROUP		MIL-STD-883 METHOD	GROUP A SUBGROUPS	READ AND RECORD
Interim Test 1	(Post Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A
Interim Test 2	2 (Post Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A
PDA (Note	1)	100% 5004	1, 7, 9, Deltas	
Interim Test 3 (Post Burn-In)		100% 5004	1, 7, 9	IDD, IOL5, IOH5A
PDA (Note	PDA (Note 1)		1, 7, 9, Deltas	
Final Test		100% 5004	2, 3, 8A, 8B, 10, 11	
Group A		Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11	
Group B Subgroup B-5		Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11, Deltas	Subgroups 1, 2, 3, 9, 10, 11
Subgroup B-6		Sample 5005	1, 7, 9	
Group D		Sample 5005	1, 2, 3, 8A, 8B, 9	Subgroups 1, 2 3

NOTE: 1.5% Parameteric, 3% Functional; Cumulative for Static 1 and 2.

#### **TABLE 7. TOTAL DOSE IRRADIATION**

	MIL-STD-883	TE	TEST		RECORD
CONFORMANCE GROUPS	METHOD	PRE-IRRAD POST-IRRAD		PRE-IRRAD	POST-IRRAD
Group E Subgroup 2	5005	1, 7, 9	Table 4	1, 9	Table 4

#### TABLE 8. BURN-IN AND IRRADIATION TEST CONNECTIONS

					OSCILLATOR	
FUNCTION	OPEN	GROUND	VDD	9V $\pm$ -0.5V	50kHz	25kHz
Static Burn-In 1 Note 1	1, 6, 8, 13	2-5, 7, 9-12	14			
Static Burn-In 2 Note 1	1, 6, 8, 13	7	2-5, 9-12, 14			
Dynamic Burn- In Note 1	6, 8	7	14	1, 13	2-5, 9-12	
Irradiation Note 2	1, 6, 8, 13	7	2-5, 9-12, 14			

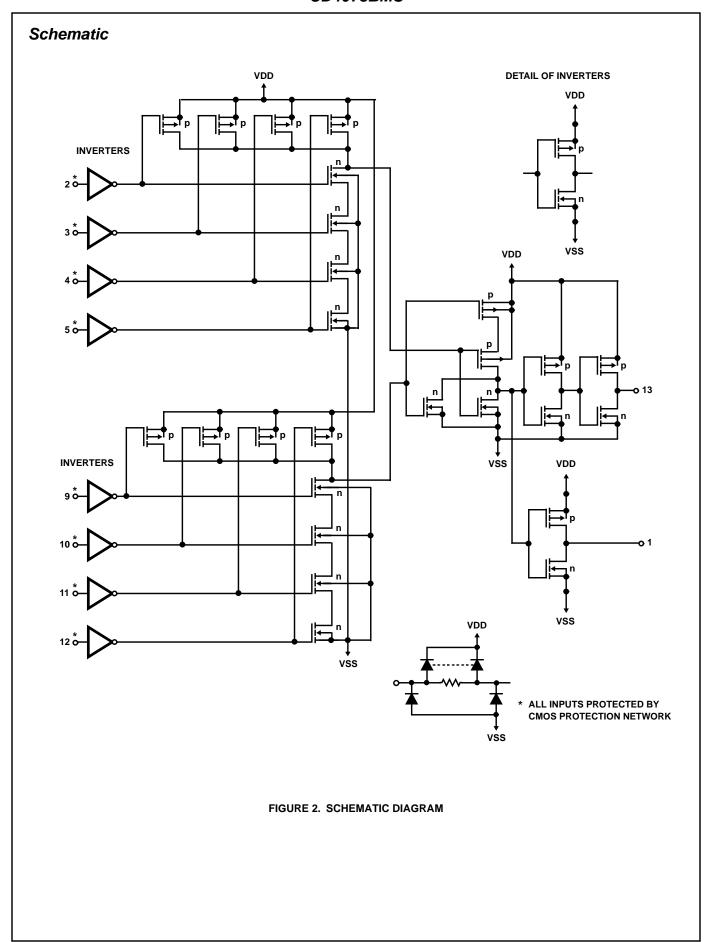
#### NOTE:

- 1. Each pin except VDD and GND will have a series resistor of 10K  $\pm$  5%, VDD = 18V  $\pm$  0.5V
- 2. Each pin except VDD and GND will have a series resistor of 47K  $\pm$  5%; Group E, Subgroup 2, sample size is 4 dice/wafer, 0 failures, VDD = 10V  $\pm$  0.5V

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# Typical Performance Characteristics

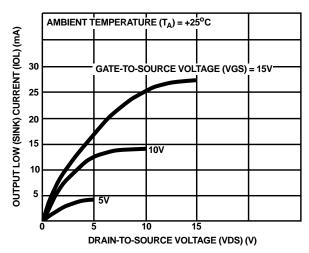


FIGURE 3. TYPICAL OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

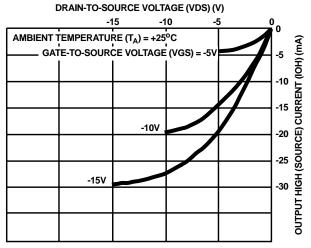


FIGURE 5. TYPICAL OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

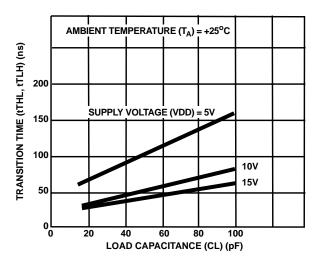


FIGURE 7. TYPICAL TRANSITION TIME AS A FUNCTION OF LOAD CAPACITANCE

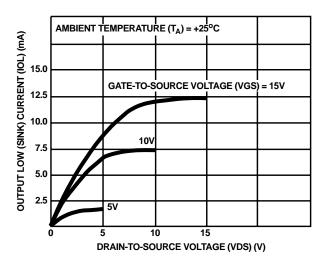


FIGURE 4. MINIMUM OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

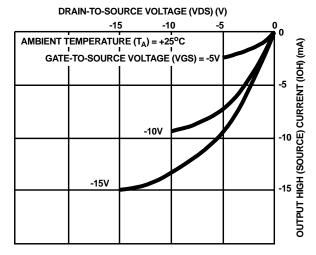


FIGURE 6. MINIMUM OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

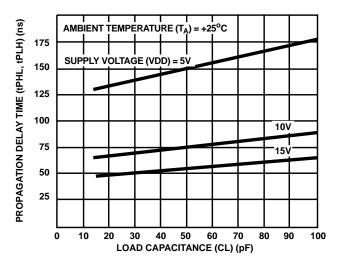


FIGURE 8. TYPICAL PROPAGATION DELAY TIME AS A FUNCTION OF LOAD CAPACITANCE

# Typical Performance Characteristics (Continued)

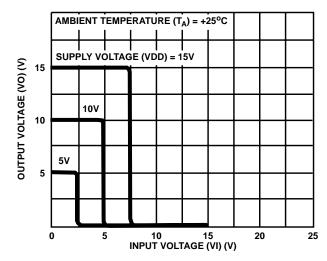


FIGURE 9. TYPICAL PROPAGATION DELAY TIME AS A FUNCTION OF SUPPLY VOLTAGE

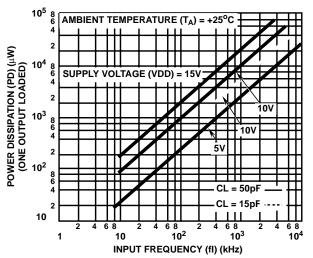
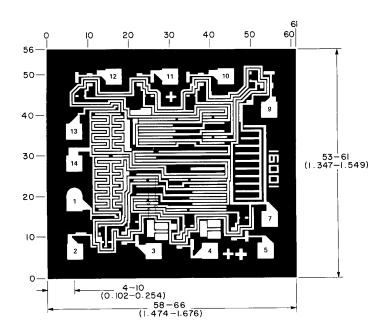


FIGURE 10. TYPICAL DYNAMIC POWER DISSIPATION AS A FUNCTION OF INPUT FREQUENCY

# Chip Dimensions and Pad Layout



Dimensions in parenthesis are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils ( $10^{-3}$  inch).

**METALLIZATION:** Thickness: 11kÅ – 14kÅ, AL.

PASSIVATION: 10.4kÅ - 15.6kÅ, Silane

**BOND PADS:** 0.004 inches X 0.004 inches MIN **DIE THICKNESS:** 0.0198 inches - 0.0218 inches

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